

# N-Channel Logic Level Enhancement Mode Power MOSFET

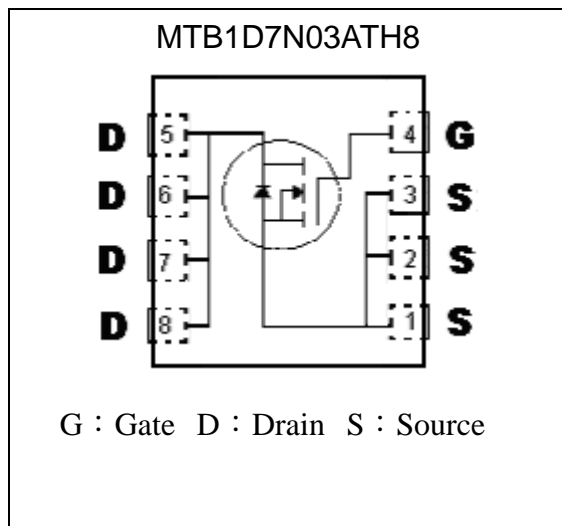
## MTB1D7N03ATH8

<b>BV<sub>DSS</sub></b>	<b>30V</b>
<b>I<sub>D</sub> @ V<sub>GS</sub>=10V, T<sub>C</sub>=25°C</b>	<b>90A</b>
<b>R<sub>DS(ON)</sub>@ V<sub>GS</sub>=10V, I<sub>D</sub>=30A</b>	<b>1.5 mΩ (typ)</b>
<b>R<sub>DS(ON)</sub>@ V<sub>GS</sub>=4.5V, I<sub>D</sub>=20A</b>	<b>2.1 mΩ (typ)</b>

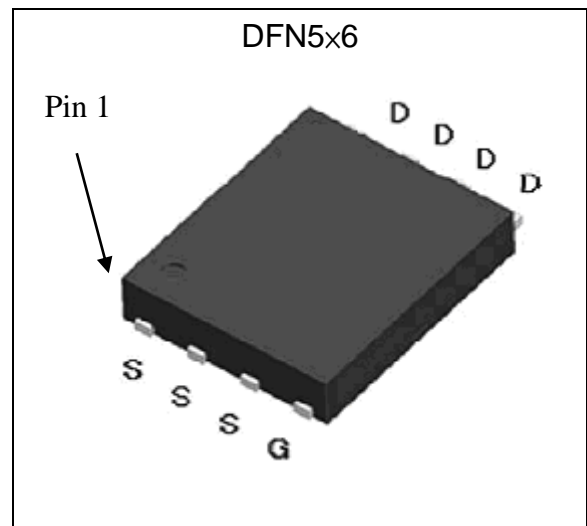
### Features

- Single Drive Requirement
- Low On-resistance
- Fast Switching Characteristic
- Pb-free lead plating and Halogen-free package

### Symbol

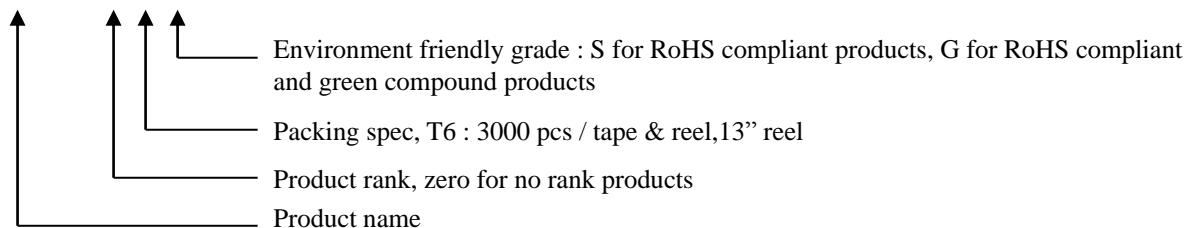


### Outline



### Ordering Information

Device	Package	Shipping
MTB1D7N03ATH8-0-T6-G	DFN 5 ×6 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel





**Absolute Maximum Ratings (Ta=25°C)**

Parameter	Symbol	Limits	Unit	
Drain-Source Voltage	V <sub>DS</sub>	30	V	
Gate-Source Voltage	V <sub>GS</sub>	±20		
Continuous Drain Current @ T <sub>C</sub> =25°C, V <sub>GS</sub> =10V	I <sub>D</sub>	90	A	
Continuous Drain Current @ T <sub>C</sub> =100°C, V <sub>GS</sub> =10V		57		
Continuous Drain Current @ T <sub>A</sub> =25°C, V <sub>GS</sub> =10V		20		
Continuous Drain Current @ T <sub>A</sub> =70°C, V <sub>GS</sub> =10V		16		
Pulsed Drain Current	I <sub>DM</sub>	360 *1		
Avalanche Current	I <sub>AS</sub>	77		
Avalanche Energy @ L=1mH, I <sub>D</sub> =30A, R <sub>G</sub> =25Ω	E <sub>AS</sub>	450	mJ	
Total Power Dissipation	P <sub>D</sub>	T <sub>C</sub> =25°C	50	W
		T <sub>C</sub> =100°C	20	
		T <sub>A</sub> =25°C	2.5	
		T <sub>A</sub> =70°C	1.6	
Operating Junction and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-55~+150	°C	

**Thermal Data**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R <sub>th,j-c</sub>	2.5	°C/W
Thermal Resistance, Junction-to-ambient, max	R <sub>th,j-a</sub>	50 *3	°C/W

- Note : 1. Pulse width limited by maximum junction temperature  
 2. Duty cycle ≤ 1%  
 3. Surface mounted on 1 in<sup>2</sup> copper pad of FR-4 board, t ≤ 10s; 125°C/W when mounted on minimum copper pad.

**Characteristics (Tc=25°C, unless otherwise specified)**

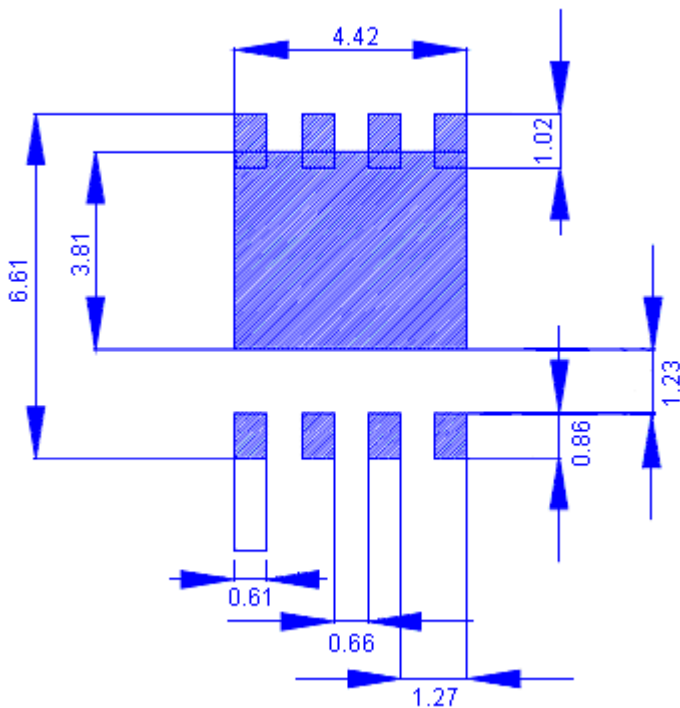
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
<b>Static</b>					
BV <sub>DSS</sub>	30	-	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA
V <sub>GS(th)</sub>	1.0	1.9	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA
G <sub>FS</sub> *1	-	58	-	S	V <sub>DS</sub> =5V, I <sub>D</sub> =20A
I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> =±20V
I <sub>DSS</sub>	-	-	1	μA	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V
	-	-	25		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>j</sub> =125°C
R <sub>DS(ON)</sub> *1	-	1.5	2.2	mΩ	V <sub>GS</sub> =10V, I <sub>D</sub> =30A
	-	2.1	4.0	mΩ	V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A
<b>Dynamic</b>					
C <sub>iss</sub>	-	5385	-	pF	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz
C <sub>oss</sub>	-	935	-		
C <sub>rss</sub>	-	854	-		

**Characteristics (Tc=25°C, unless otherwise specified)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Qg *1, 2	-	53	-	nC	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A
Qgs *1, 2	-	16	-		
Qgd *1, 2	-	25	-		
t <sub>d(ON)</sub> *1, 2	-	16	-	ns	V <sub>DS</sub> =15V, I <sub>D</sub> =1A, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω
tr *1, 2	-	21	-		
t <sub>d(OFF)</sub> *1, 2	-	76	-		
t <sub>f</sub> *1, 2	-	32	-		
R <sub>g</sub>	-	1.6	-	Ω	V <sub>GS</sub> =15mV, V <sub>DS</sub> =0V, f=1MHz
<b>Source-Drain Diode</b>					
I <sub>S</sub> *1	-	-	90	A	
I <sub>SM</sub> *3	-	-	360		
V <sub>SD</sub> *1	-	0.79	1.2	V	I <sub>S</sub> =20A, V <sub>GS</sub> =0V
trr	-	28	-	ns	I <sub>F</sub> =20A, dI <sub>F</sub> /dt=100A/μs
Q <sub>rr</sub>	-	23	-	nC	

Note : \*1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%  
 \*2.Independent of operating temperature  
 \*3.Pulse width limited by maximum junction temperature.

**Recommended Soldering Footprint**

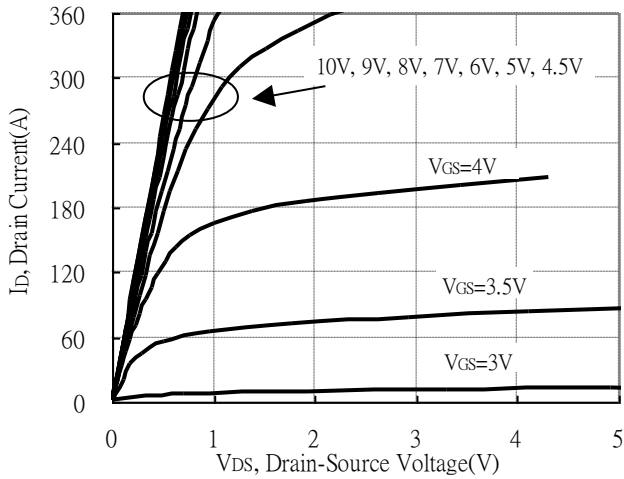


unit : mm

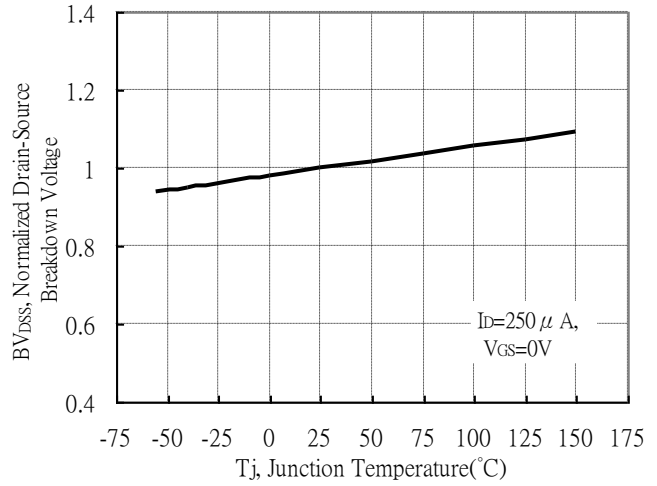


**Typical Characteristics**

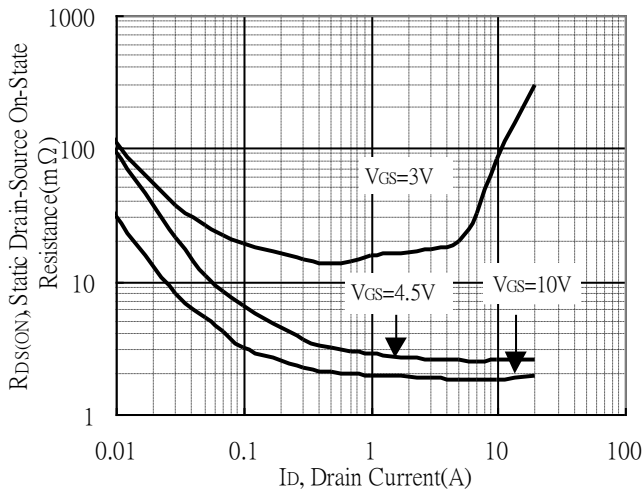
Typical Output Characteristics



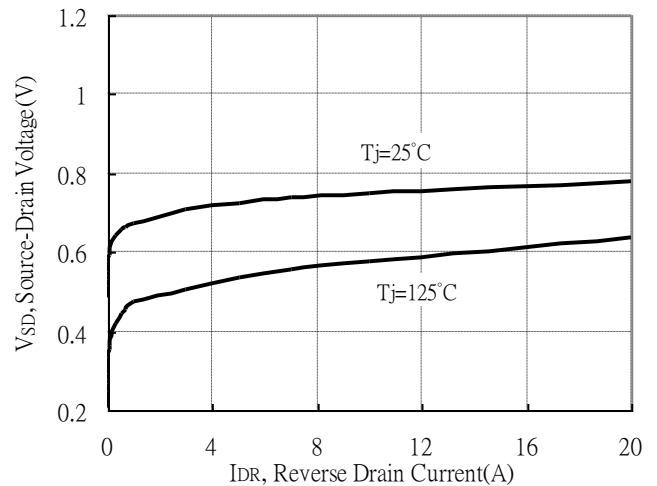
Brekdown Voltage vs Ambient Temperature



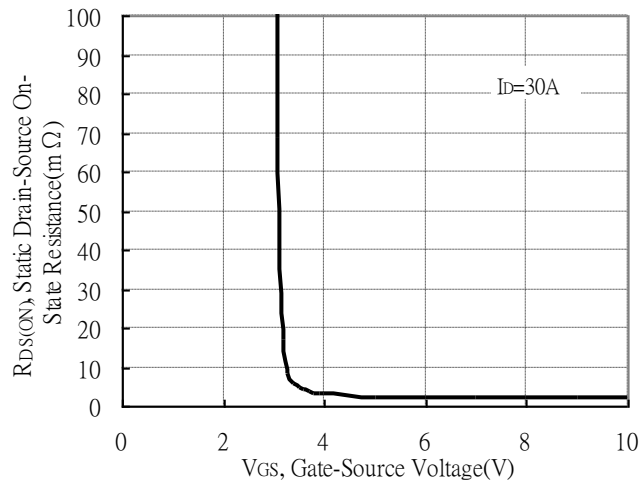
Static Drain-Source On-State resistance vs Drain Current



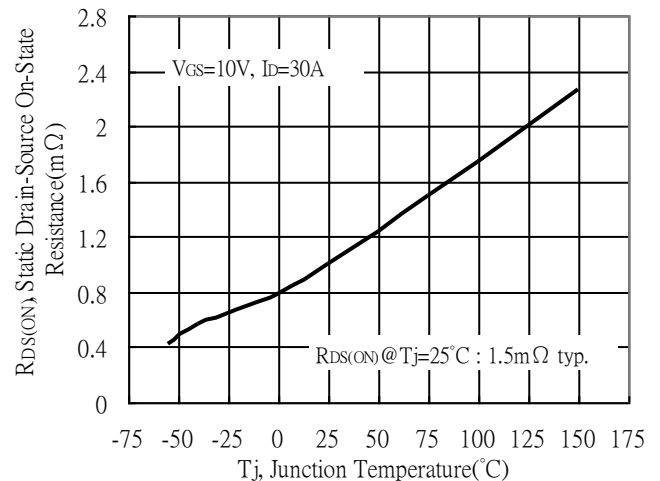
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

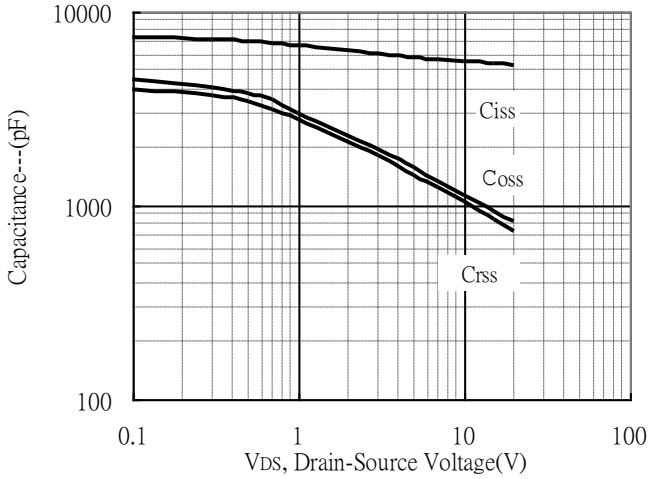


Drain-Source On-State Resistance vs Junction Temperature

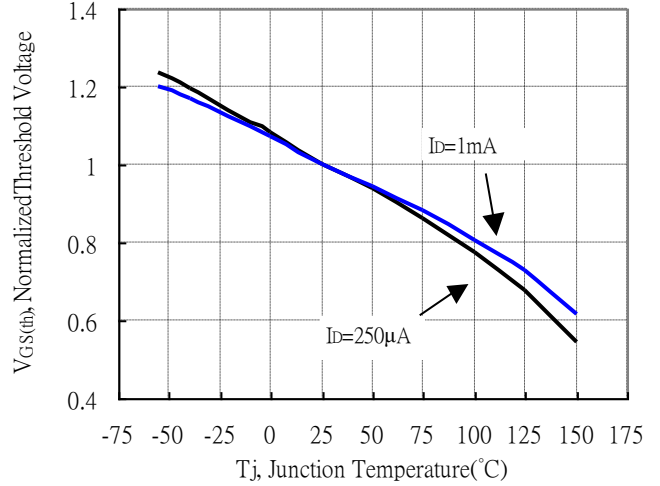


**Typical Characteristics(Cont.)**

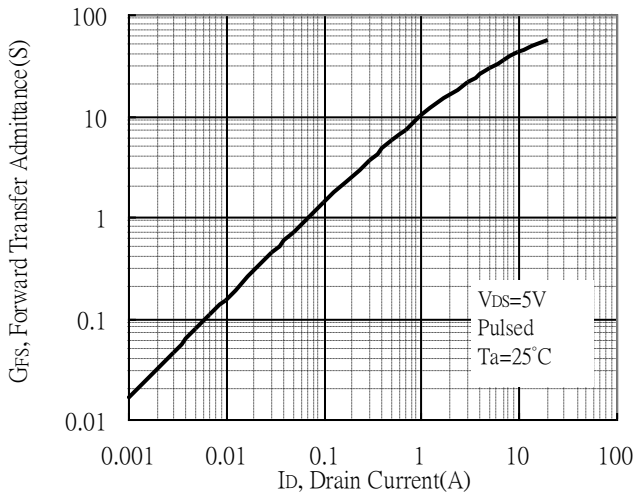
Capacitance vs Drain-to-Source Voltage



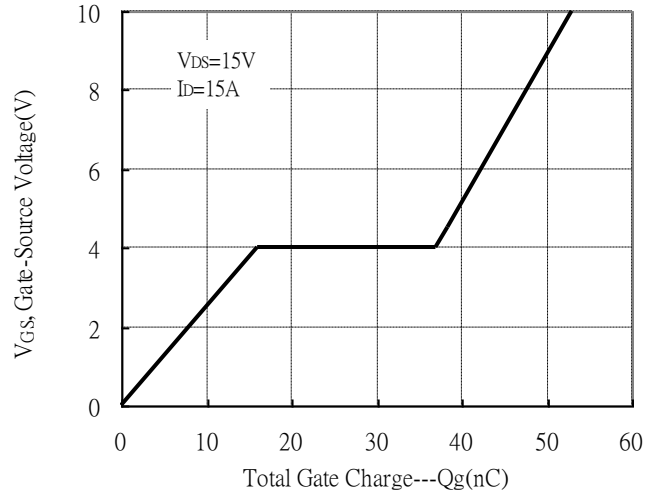
Threshold Voltage vs Junction Temperature



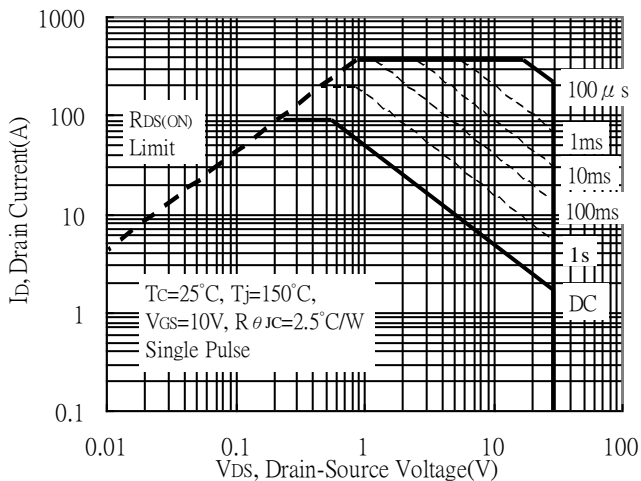
Forward Transfer Admittance vs Drain Current



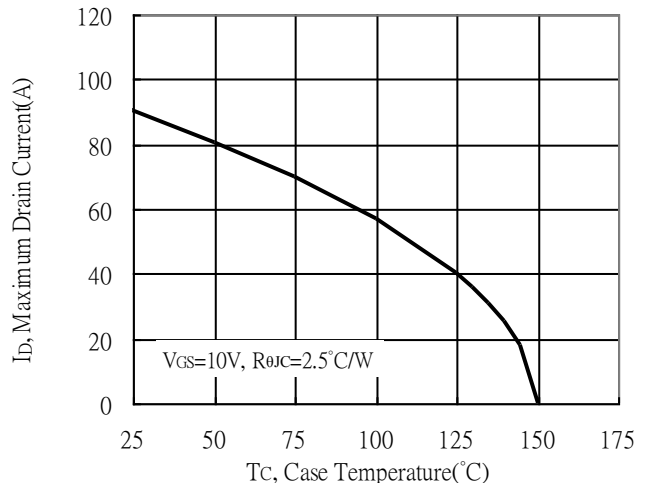
Gate Charge Characteristics



Maximum Safe Operating Area



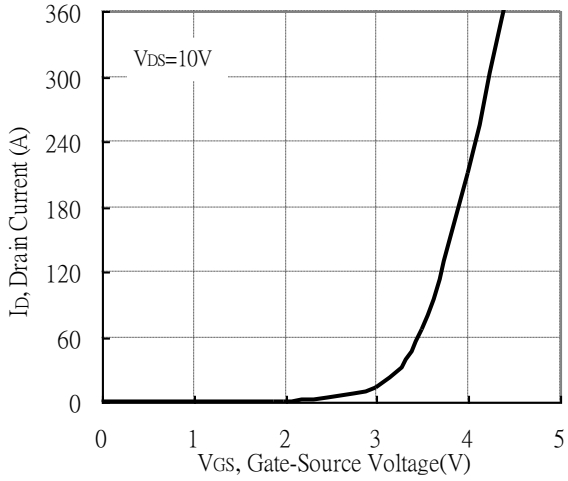
Maximum Drain Current vs Case Temperature



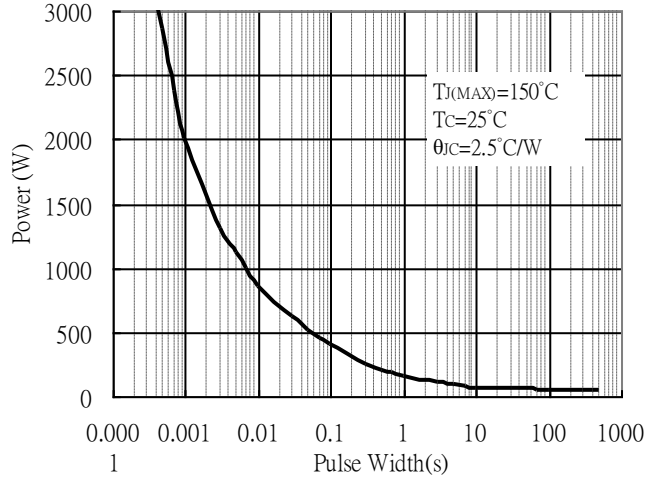


### Typical Characteristics(Cont.)

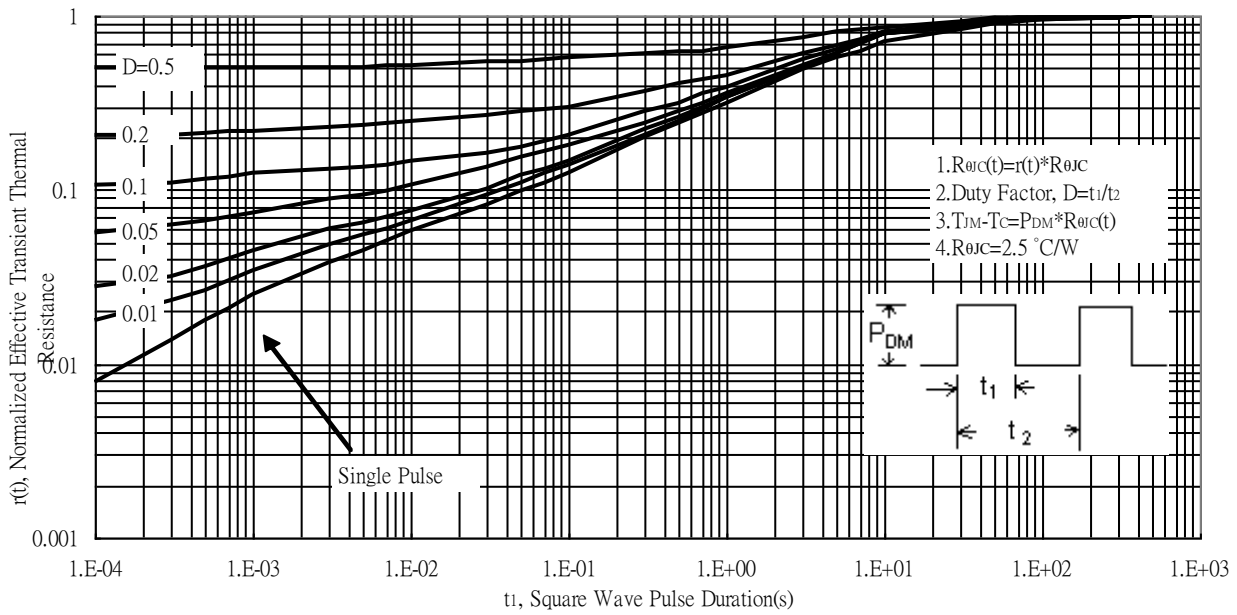
Typical Transfer Characteristics



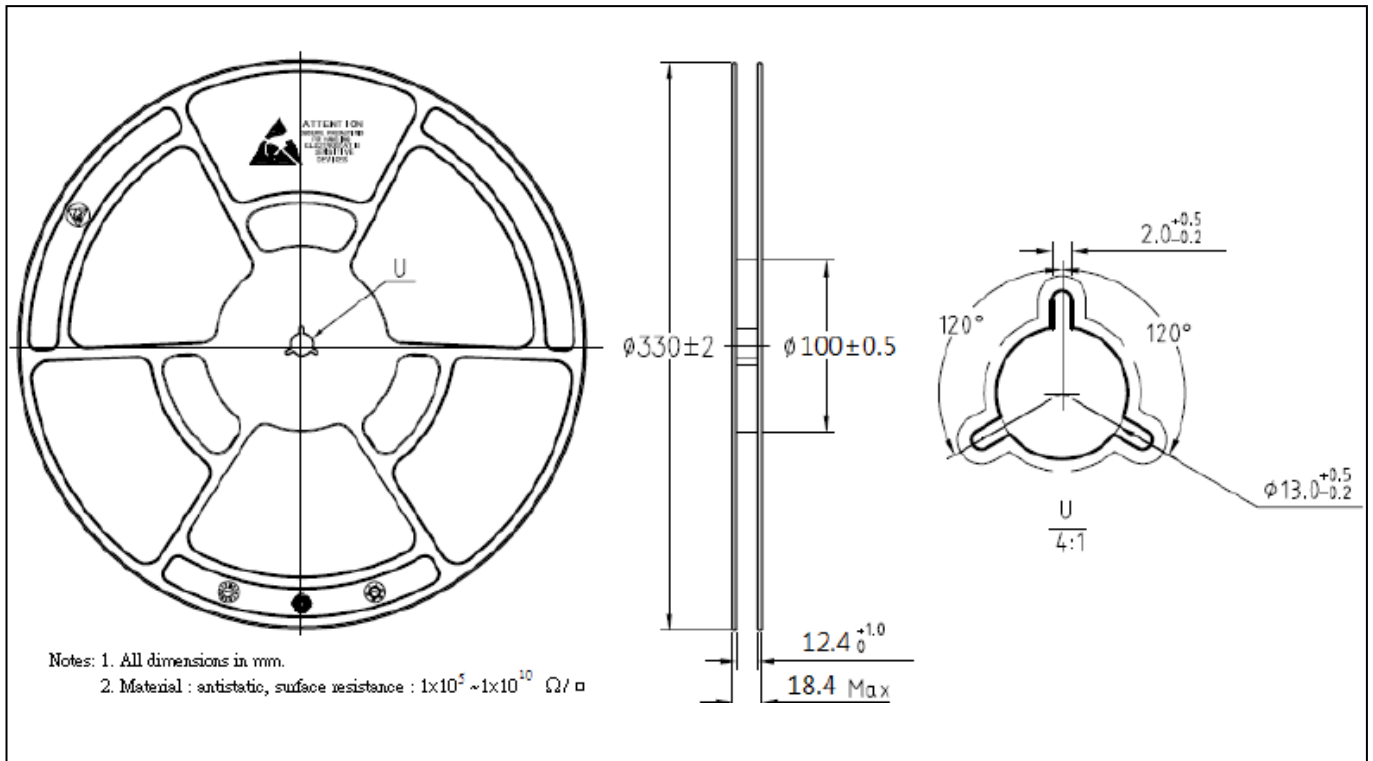
Single Pulse Maximum Power Dissipation



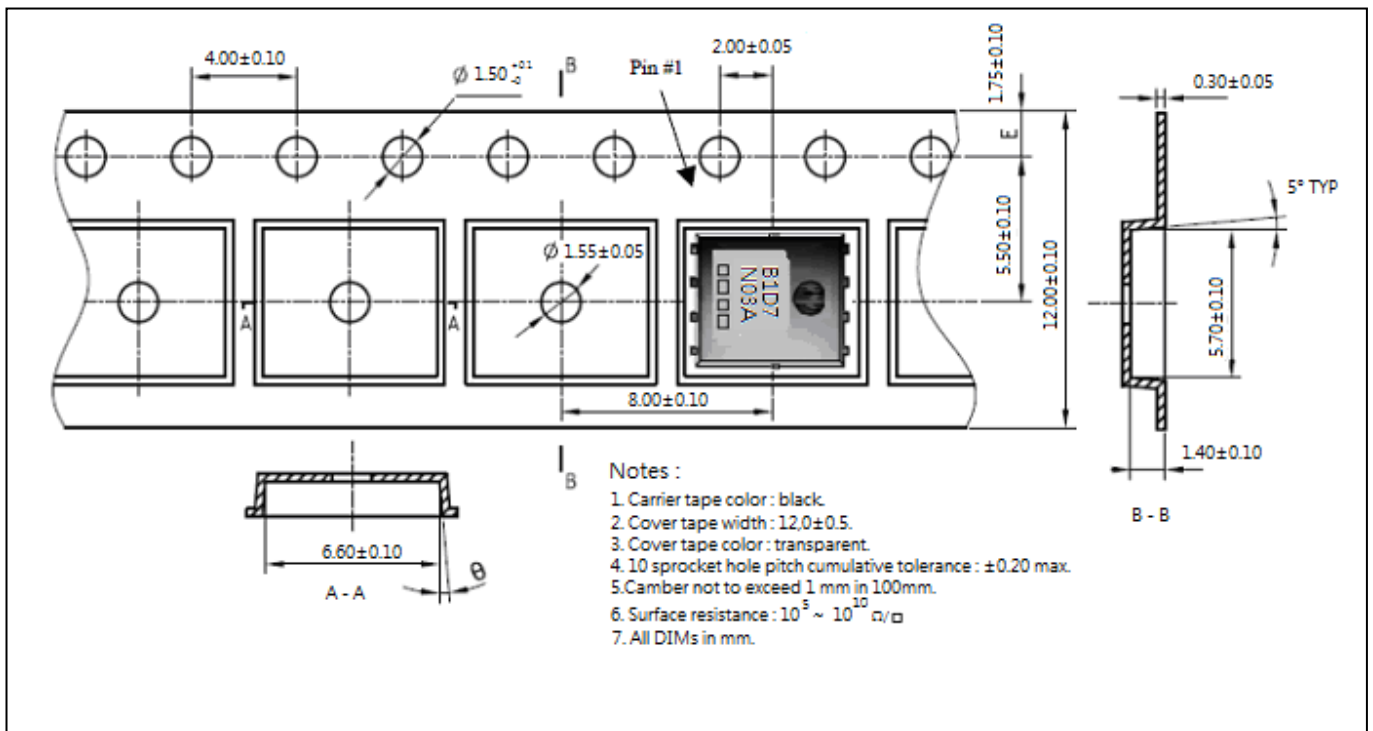
Transient Thermal Response Curves



**Reel Dimension**



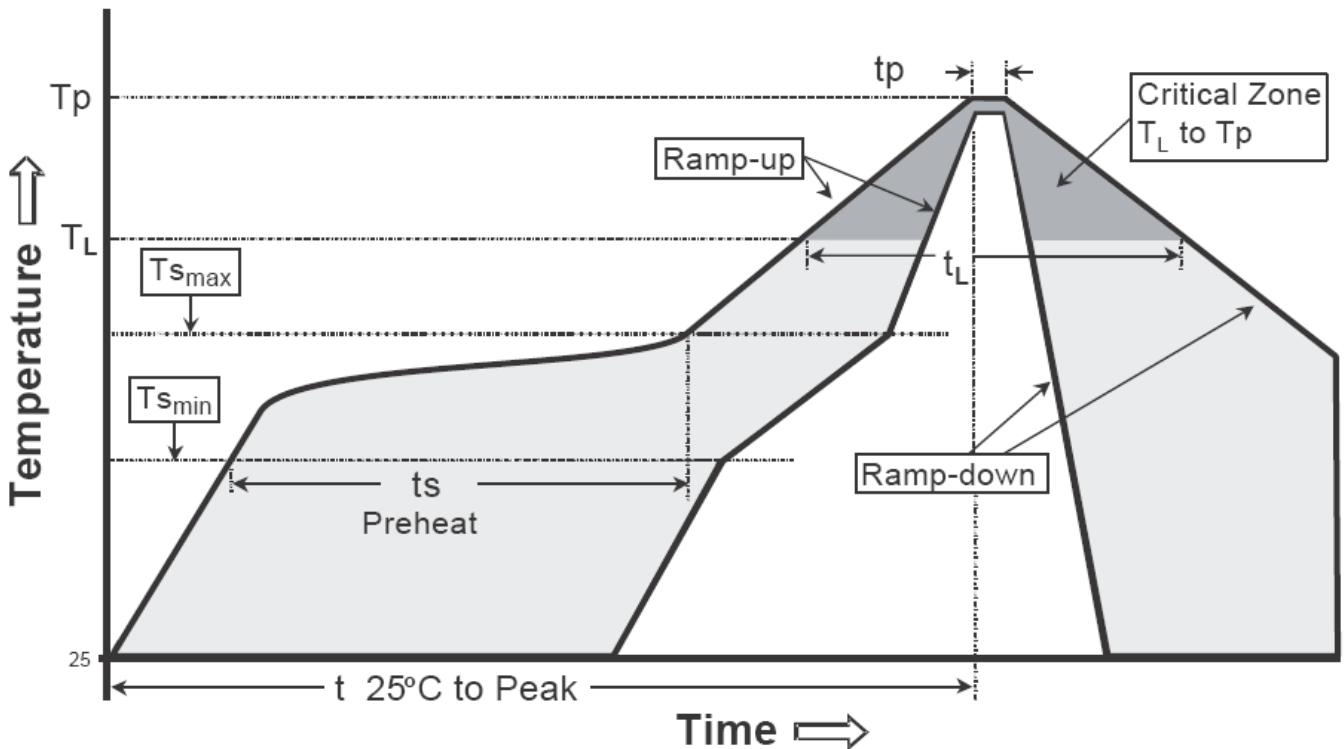
**Carrier Tape Dimension**



**Recommended wave soldering condition**

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

**Recommended temperature profile for IR reflow**

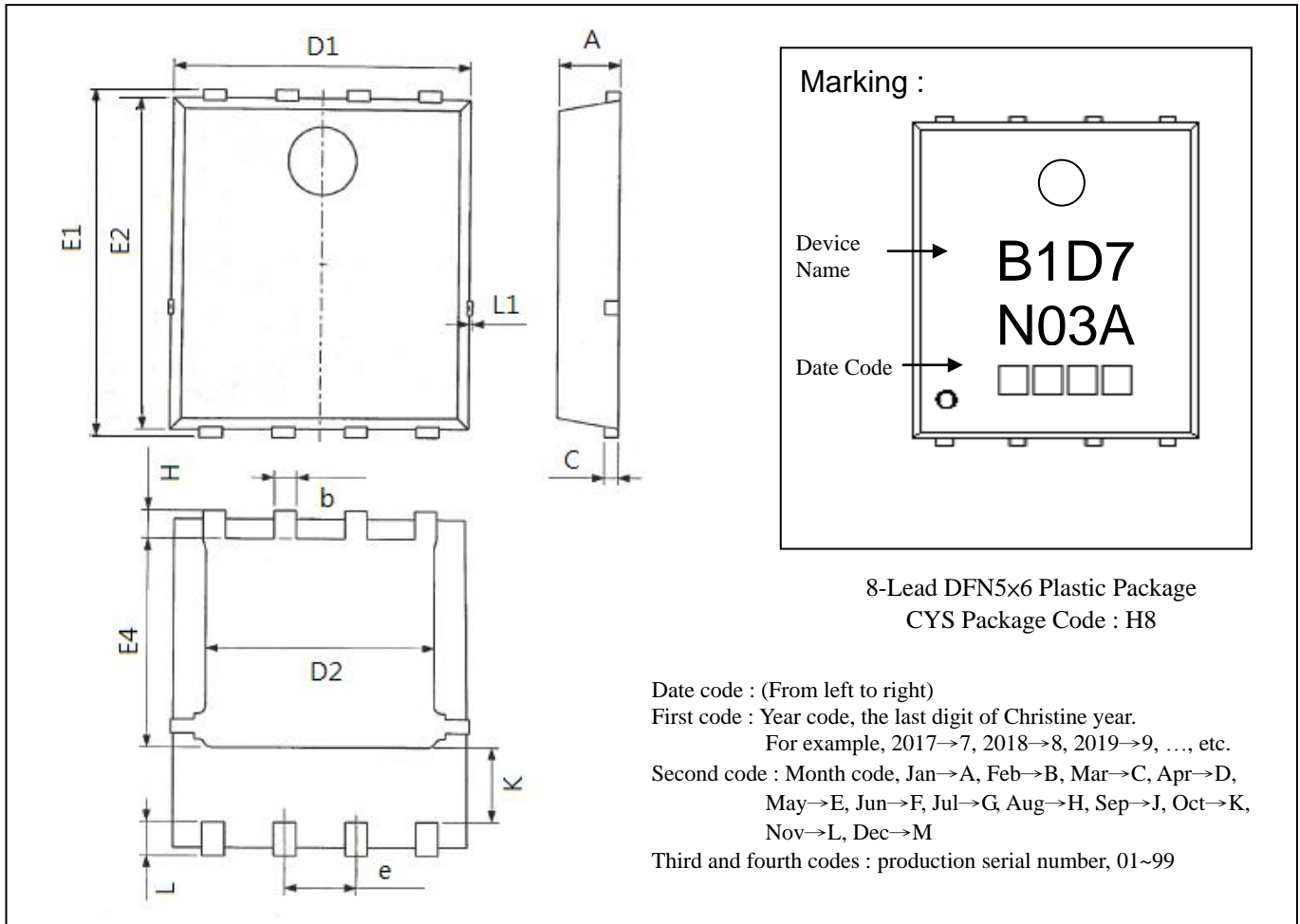


Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T <sub>smax</sub> to T <sub>p</sub> )	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T <sub>s min</sub> )	100°C	150°C
-Temperature Max(T <sub>s max</sub> )	150°C	200°C
-Time(t <sub>s min</sub> to t <sub>s max</sub> )	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T <sub>L</sub> )	183°C	217°C
- Time (t <sub>L</sub> )	60-150 seconds	60-150 seconds
Peak Temperature(T <sub>p</sub> )	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.



**DFN5x6 Dimension**



**Marking :**

Device Name → **B1D7**  
 N03A  
 Date Code → 0111

8-Lead DFN5x6 Plastic Package  
 CYS Package Code : H8

Date code : (From left to right)  
 First code : Year code, the last digit of Christine year.  
 For example, 2017→7, 2018→8, 2019→9, ..., etc.  
 Second code : Month code, Jan→A, Feb→B, Mar→C, Apr→D,  
 May→E, Jun→F, Jul→G, Aug→H, Sep→J, Oct→K,  
 Nov→L, Dec→M  
 Third and fourth codes : production serial number, 01~99

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	1.000	1.200	0.0394	0.0472	E2	5.660	6.060	0.2228	0.2386
b	0.300	0.500	0.0118	0.0197	E4	3.520	3.920	0.1386	0.1543
C	0.154	0.354	0.0061	0.0139	H	0.400	0.600	0.0157	0.0236
D1	5.000	5.400	0.1969	0.2126	K	1.150	1.450	0.0453	0.0571
D2	3.800	4.250	0.1496	0.1673	L	0.300	0.700	0.0118	0.0276
e	1.170	1.370	0.0461	0.0539	L1	0.000	0.120	0.0000	0.0047
E1	5.950	6.350	0.2343	0.2500					

**Notes:** 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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